

BFU610F

NPN wideband silicon germanium RF transistor

Rev. 01 — 17 June 2010

Objective data sheet

1. Product profile

1.1 General description

NPN silicon germanium microwave transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT343F package.

1.2 Features and benefits

- 40 GHz f_T silicon germanium technology
- High associated gain 12 dB at 12 GHz
- Low noise high gain microwave transistor
- Noise figure (NF) = 1.4 dB at 5.8 GHz

1.3 Applications

- 2nd LNA stage and mixer stage in DBS LNB's
- Analog/digital cordless applications
- Ka band oscillators DRO's
- Low noise amplifiers for microwave communications systems
- Satellite radio
- WLAN and CDMA applications

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|----------------------------|--|-----|-----|------|------|
| C_{CBS} | collector-base capacitance | $V_{CB} = 2 \text{ V}$; $f = 1 \text{ MHz}$; $V_{BE} = [\text{tbd}] \text{ V}$ | - | 70 | - | fF |
| f_T | transition frequency | $V_{CE} = 2 \text{ V}$; $I_C = 25 \text{ mA}$; $f = 2 \text{ GHz}$; $T_{amb} = 25 \text{ }^\circ\text{C}$ | - | 40 | - | GHz |
| $G_{p(\text{max})}$ | maximum power gain | $f = 5.8 \text{ GHz}$; $I_C = 8 \text{ mA}$; $V_{CE} = 2 \text{ V}$; $T_{amb} = 25 \text{ }^\circ\text{C}$ | [1] | - | 21 | dB |
| h_{FE} | DC current gain | $V_{CE} = 2 \text{ V}$; $I_C = 10 \text{ mA}$; $T_j = 25 \text{ }^\circ\text{C}$ | 70 | 140 | 270 | |
| I_C | collector current | | - | - | 10 | mA |
| P_{tot} | total power dissipation | $T_{sp} \leq 90 \text{ }^\circ\text{C}$; see Figure 1 | [2] | - | 50 | mW |
| V_{CBO} | collector-base voltage | $I_E = 0 \text{ A}$ | - | - | 10 | V |
| V_{CEO} | collector-emitter voltage | $I_B = 0 \text{ A}$ | - | - | 5 | V |
| V_{EBO} | emitter-base voltage | $I_C = 0 \text{ A}$ | - | - | 0.55 | V |

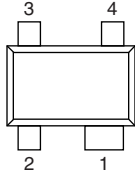
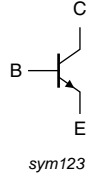
[1] $G_{p(\text{max})}$ is the maximum power gain, if $K > 1$. If $K < 1$ then $G_{p(\text{max})} = \text{MSG}$.

[2] T_{sp} is the temperature at the solder point of the emitter lead.



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|---|---|
| 1 | E | emitter |  |  |
| 2 | B | base | | |
| 3 | E | emitter | | |
| 4 | C | collector | | |

SOT343F (DFP4)

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BFU610F | DFP4 | Plastic surface-mounted flat pack package; 4 leads | SOT343F |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BFU610F | D1 |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------|---------------------------|---|-----|-----|------|------|
| V_{CBO} | collector-base voltage | $I_E = 0$ A | - | - | 10 | V |
| V_{CEO} | collector-emitter voltage | $I_B = 0$ A | - | - | 5 | V |
| V_{EBO} | emitter-base voltage | $I_C = 0$ A | - | - | 0.55 | V |
| I_C | collector current | | - | - | 10 | mA |
| P_{tot} | total power dissipation | $T_{sp} \leq 90$ °C; see Figure 1 | | | 50 | mW |
| T_{stg} | storage temperature | | -65 | - | 150 | °C |
| T_j | junction temperature | | - | - | 150 | °C |

[1] T_{sp} is the temperature at the solder point of the emitter lead.

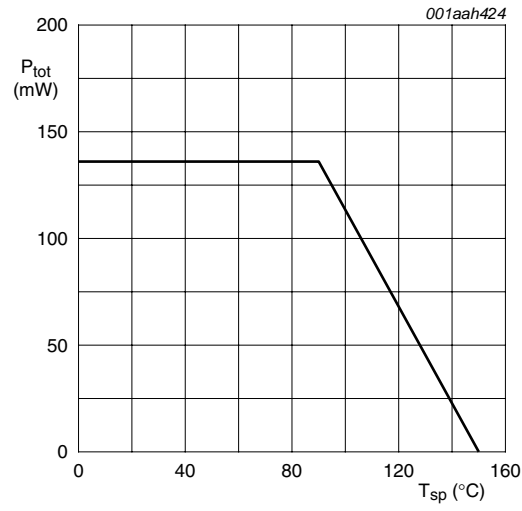


Fig 1. Power derating curve

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|--|------------|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | - | 440 | - | K/W |

7. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit | |
|---------------------|---------------------------------------|--|-----|-------|------|------|----|
| $V_{(BR)CBO}$ | collector-base breakdown voltage | $I_E = 0 \text{ mA}; I_C = 2.5 \text{ } \mu\text{A}; T_j = 25 \text{ } ^\circ\text{C}$ | 10 | - | - | V | |
| $V_{(BR)CEO}$ | collector-emitter breakdown voltage | $I_B = 0 \text{ mA}; I_C = 1 \text{ mA}; T_j = 25 \text{ } ^\circ\text{C}$ | 5 | - | - | V | |
| I_{CBO} | collector-base cut-off current | $I_E = 0 \text{ mA}; V_{CB} = 4.5 \text{ V}; T_j = 25 \text{ } ^\circ\text{C}$ | - | - | 100 | nA | |
| h_{FE} | DC current gain | $V_{CE} = 2 \text{ V}; I_C = 10 \text{ mA}; T_j = 25 \text{ } ^\circ\text{C}$ | 70 | 140 | 270 | | |
| C_{CBS} | collector-base capacitance | $V_{CB} = 2 \text{ V}; f = 1 \text{ MHz}; V_{BE} = [\text{tbd}] \text{ V}$ | - | 70 | - | fF | |
| f_T | transition frequency | $V_{CE} = 2 \text{ V}; I_C = 25 \text{ mA}; f = 2 \text{ GHz}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | - | 40 | - | GHz | |
| $G_{p(\text{max})}$ | maximum power gain | $f = 5.8 \text{ GHz}; I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | [1] | - | 21 | - | dB |
| | | $f = 1.8 \text{ GHz}; I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | [1] | - | 29 | - | dB |
| | | $f = 1.5 \text{ GHz}; I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | [1] | - | 30.4 | - | dB |
| | | $f = 2.4 \text{ GHz}; I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | [1] | - | 28 | - | dB |
| | | $f = 12 \text{ GHz}; I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | [1] | - | 14.3 | - | dB |
| $ s_{21} ^2$ | insertion power gain | $I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; f = 1.5 \text{ GHz}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | - | 19 | - | dB | |
| | | $I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; f = 1.8 \text{ GHz}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | - | 18 | - | dB | |
| | | $I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; f = 2.4 \text{ GHz}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | - | 17.5 | - | dB | |
| | | $I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; f = 5.8 \text{ GHz}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | - | 13.4 | - | dB | |
| | | $I_C = 8 \text{ mA}; V_{CE} = 2 \text{ V}; f = 12 \text{ GHz}; T_{amb} = 25 \text{ } ^\circ\text{C}$ | - | 7.7 | - | dB | |
| $P_{L(1\text{dB})}$ | output power at 1 dB gain compression | $V_{CE} = 2 \text{ V}; f = 1.5 \text{ GHz}; I_C = 25 \text{ mA}; Z_L = 50 \text{ } \Omega; Z_S = 50 \text{ } \Omega$ | - | [tbd] | - | dBmW | |
| | | $V_{CE} = 2 \text{ V}; f = 2.4 \text{ GHz}; I_C = 25 \text{ mA}; Z_L = 50 \text{ } \Omega; Z_S = 50 \text{ } \Omega$ | - | [tbd] | - | dBmW | |
| | | $V_{CE} = 2 \text{ V}; f = 1.8 \text{ GHz}; I_C = 25 \text{ mA}; Z_L = 50 \text{ } \Omega; Z_S = 50 \text{ } \Omega$ | - | [tbd] | - | dBmW | |
| | | $V_{CE} = 2 \text{ V}; f = 5.8 \text{ GHz}; I_C = 25 \text{ mA}; Z_L = 50 \text{ } \Omega; Z_S = 50 \text{ } \Omega$ | - | [tbd] | - | dBmW | |

[1] $G_{p(\text{max})}$ is the maximum power gain, if $K > 1$. If $K < 1$ then $G_{p(\text{max})} = \text{MSG}$.

8. Package outline

Plastic surface-mounted flat pack package; reverse pinning; 4 leads

SOT343F

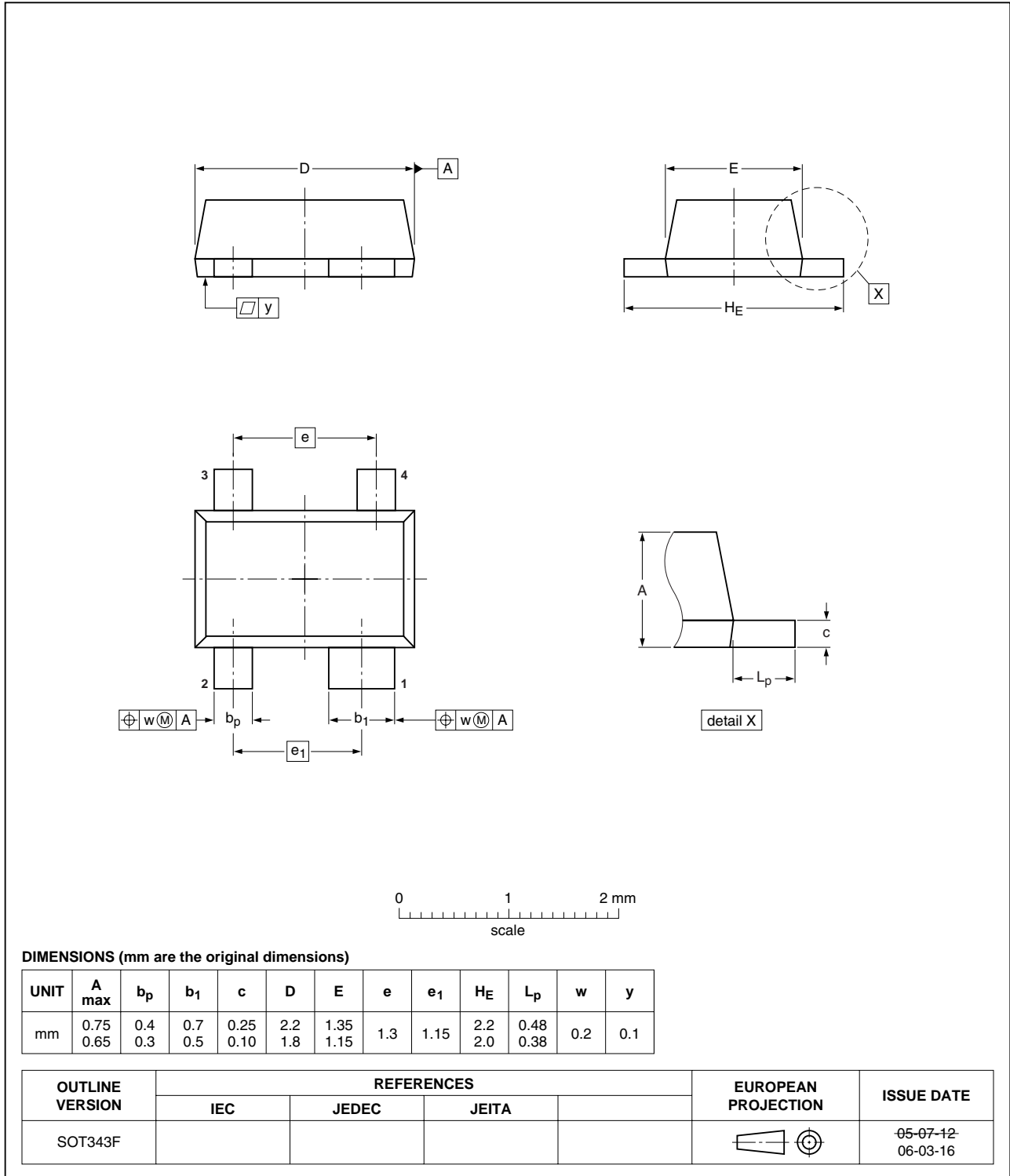


Fig 2. Package outline SOT343F (DFP4)

9. Soldering

Footprint information for reflow soldering

SOT343F

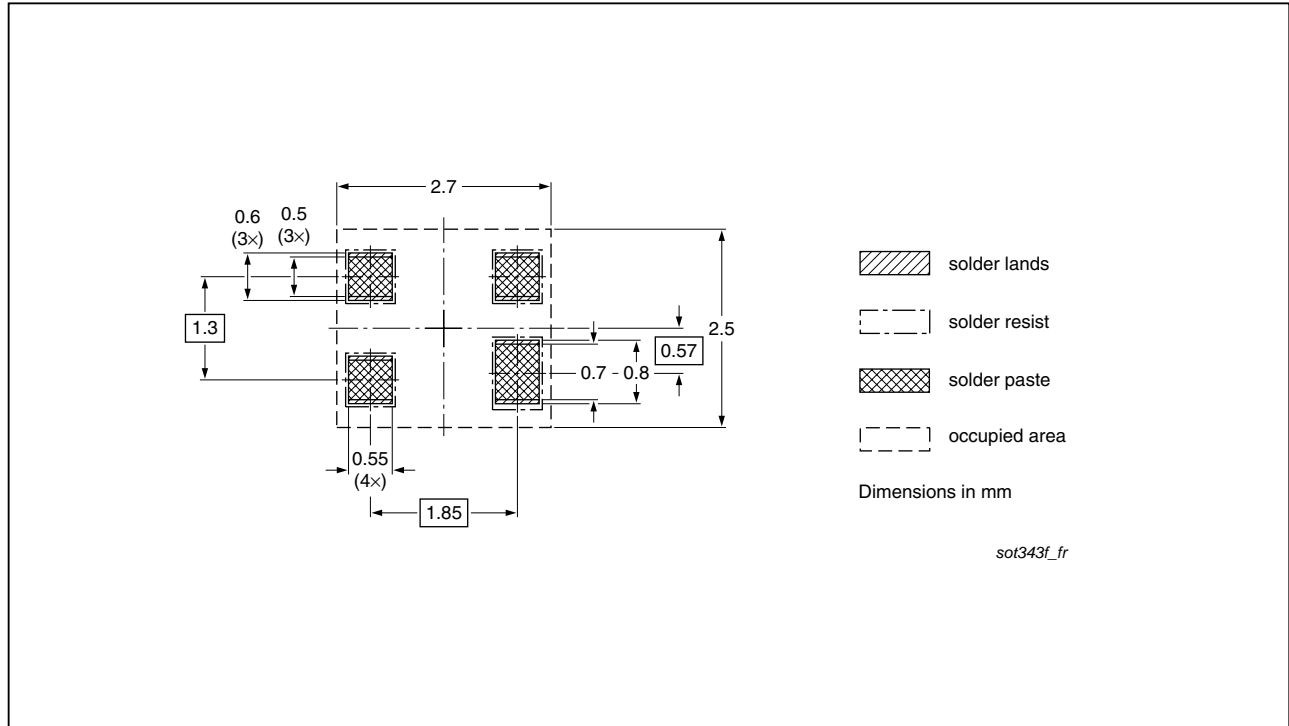


Fig 3. Reflow soldering footprint for SOT343F (DFP4)

Footprint information for wave soldering

SOT343F

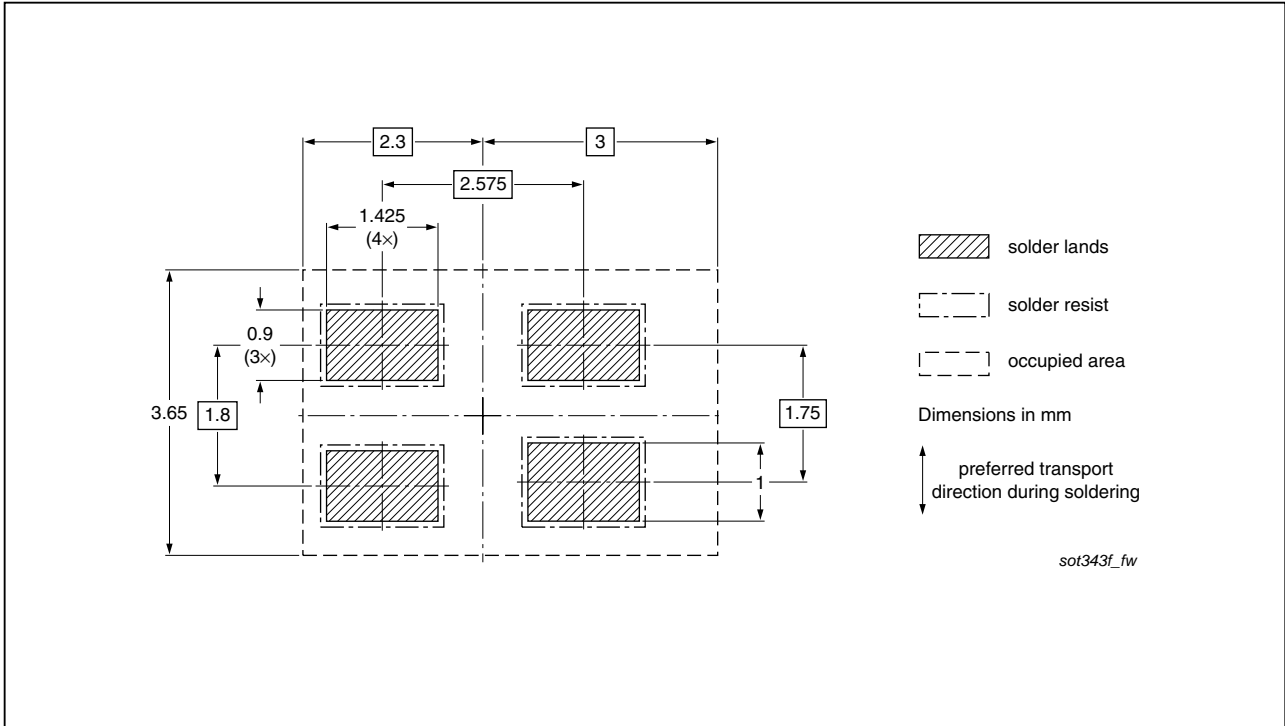


Fig 4. Wave soldering footprint for SOT343F (DFP4)

10. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|----------------------|---------------|------------|
| BFU610F v.1 | 20100617 | Objective data sheet | - | - |

11. Legal information

11.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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